

# Giriraj Jnawali

## List of Publications by Year in descending order

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34  
papers

913  
citations

566801

15  
h-index

454577

30  
g-index

35  
all docs

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docs citations

35  
times ranked

1717  
citing authors

#	ARTICLE	IF	CITATIONS
1	Band structure and polarization effects in photothermoelectric spectroscopy of a Bi <sub>2</sub> Se <sub>3</sub> device. Applied Physics Letters, 2022, 120, .	1.5	1
2	A Raman probe of phonons and electron-phonon interactions in the Weyl semimetal NbIrTe <sub>4</sub> . Scientific Reports, 2021, 11, 8155.	1.6	10
3	Hot carrier transport limits the displacive excitation of coherent phonons in bismuth. Applied Physics Letters, 2021, 119, .	1.5	3
4	Ultrafast photoinduced band splitting and carrier dynamics in chiral tellurium nanosheets. Nature Communications, 2020, 11, 3991.	5.8	39
5	Exploring the band structure of Wurtzite InAs nanowires using photocurrent spectroscopy. Nano Research, 2020, 13, 1586-1591.	5.8	7
6	Temperature-Controlled Rotational Epitaxy of Graphene. Nano Letters, 2019, 19, 4594-4600.	4.5	19
7	Strong Hot Carrier Effects in Single Nanowire Heterostructures. Nano Letters, 2019, 19, 5062-5069.	4.5	13
8	Rapid onset of strain relief by massive generation of misfit dislocations in Bi(111)/Si(001) heteroepitaxy. Applied Physics Letters, 2019, 114, 081601.	1.5	2
9	Graphene-Complex-Oxide Nanoscale Device Concepts. ACS Nano, 2018, 12, 6128-6136.	7.3	6
10	Revealing Optical Transitions and Carrier Recombination Dynamics within the Bulk Band Structure of Bi <sub>2</sub> Se <sub>3</sub> . Nano Letters, 2018, 18, 5875-5884.	4.5	21
11	Room-Temperature Quantum Transport Signatures in Graphene/LaAlO <sub>3</sub> /SrTiO <sub>3</sub> Heterostructures. Advanced Materials, 2017, 29, 1603488.	11.1	12
12	Wavelength scaling of strong field effects in GaAs. , 2017, , .		0
13	Barrier-free subsurface incorporation of atoms into Bi(111) films. Physical Review B, 2015, 91, .		
14	Observation of Ground- and Excited-State Charge Transfer at the C <sub>60</sub> /Graphene Interface. ACS Nano, 2015, 9, 7175-7185.	7.3	69
15	Electric field effects in graphene/LaAlO <sub>3</sub> /SrTiO <sub>3</sub> heterostructures and nanostructures. APL Materials, 2015, 3, 062502.	2.2	17
16	Photoconductive response of a single Au nanorod coupled to LaAlO <sub>3</sub> /SrTiO <sub>3</sub> nanowires. Applied Physics Letters, 2015, 106, .	1.5	6
17	In-situ high-resolution low energy electron diffraction study of strain relaxation in heteroepitaxy of Bi(111) on Si(001): Interplay of strain state, misfit dislocation array and lattice parameter. Thin Solid Films, 2014, 570, 159-163.	0.8	2
18	Observation of a Transient Decrease in Terahertz Conductivity of Single-Layer Graphene Induced by Ultrafast Optical Excitation. Nano Letters, 2013, 13, 524-530.	4.5	241

#	ARTICLE	IF	CITATIONS
19	Interplay between Forward and Backward Scattering of Spin-Orbit Split Surface States of Bi(111). Nano Letters, 2013, 13, 2717-2722.	4.5	25
20	Manipulation of Electronic Transport in the Bi(111) Surface State. Physical Review Letters, 2012, 108, 266804.	2.9	22
21	Interplay of Wrinkles, Strain, and Lattice Parameter in Graphene on Iridium. Nano Letters, 2012, 12, 678-682.	4.5	131
22	Anisotropic scattering of surface state electrons at a point defect on Bi(111). Applied Physics Letters, 2011, 98, .	1.5	24
23	Growth temperature dependent graphene alignment on Ir(111). Applied Physics Letters, 2011, 98, .	1.5	95
24	Lost in reciprocal space? Determination of the scattering condition in spot profile analysis low-energy electron diffraction. Review of Scientific Instruments, 2011, 82, 035111.	0.6	9
25	Two-Dimensional Electron Transport and Scattering in Bi(111) Surface States. E-Journal of Surface Science and Nanotechnology, 2010, 8, 27-31.	0.1	11
26	Epitaxial Growth of Bi(111) on Si(001). E-Journal of Surface Science and Nanotechnology, 2009, 7, 441-447.	0.1	1
27	Nucleation and initial growth in the semimetallic homoepitaxial system of Bi on Bi(111). Physical Review B, 2009, 79, .	1.1	7
28	Stable tungsten disilicide contacts for surface and thin film resistivity measurements. Journal of Vacuum Science & Technology B, 2009, 27, 180.	1.3	4
29	Nanoscale dislocation patterning in Bi(111)/Si(001) heteroepitaxy. Surface Science, 2009, 603, 2057-2061.	0.8	8
30	Epitaxial Bi(111) films on Si(001): Strain state, surface morphology, and defect structure. Thin Solid Films, 2008, 516, 8227-8231.	0.8	18
31	Homoepitaxial growth of Bi(111). Physical Review B, 2008, 78, .	1.1	19
32	Lattice-matching periodic array of misfit dislocations: Heteroepitaxy of Bi(111) on Si(001). Physical Review B, 2007, 76, .	1.1	18
33	Nanopattern Formation by Periodic Array of Interfacial Misfit Dislocations in Bi(111)/Si(001) Heteroepitaxy. Materials Research Society Symposia Proceedings, 2007, 1059, 1.	0.1	2
34	Lattice accommodation of epitaxial Bi(111) films on Si(001) studied with SPA-LEED and AFM. Physical Review B, 2006, 74, .	1.1	42